

8/27/2003

SC12804TP

PTO/SB/08A (04-03)

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete If Known		
		Application Number	10/450,002	
		Filing Date	Concurrently Herewith 8/27/2003	
		First Named Inventor	Varughese Mathew et al.	
		Group Art Unit	2825	
Examiner Name	C. Everhart			
Sheet		of	Attorney Docket Number	SC12804TP

U. S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number -Kind Code ² (if known)			
AME	AA	5,695,810	12/09/1997	Dubin <i>et al.</i>	—
CME	AB	2003/0113576 A1	06/19/2003	Chebiam <i>et al.</i>	—
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FOREIGN PATENT DOCUMENTS							
Examine r Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴ Kind Code ² (if known)				
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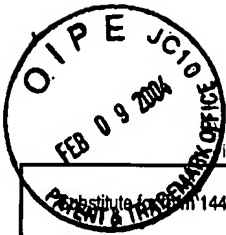
NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CME	AC	Itabashi <i>et al.</i> , "Electroless Deposited CoWB for Copper Diffusion Barrier Metal," <i>Proceedings of the IEEE 2002 International Interconnect Technology Conference (Cat. No. 02EX519)</i> , 2002, pp. 285-287.	

Examiner Signature	C. Everhart	Date Considered	10-29-04
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¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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PTO/SB/08A (04-03)

INSTITUTE FOR INVENTORS 1449A/PTO		Complete if Known			
		Application Number	10/650,002		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Filing Date	August 27, 2003		
		First Named Inventor	Varughese Mathew et al.		
		Group Art Unit	1762 2825		
		Examiner Name	Unassigned C. Everhart		
Sheet		of		Attorney Docket Number	SC12804TP

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		Number -Kind Code ² (if known)			
CME	BA	6,528,409 B1	03/04/2003	Lopatin et al.	—
CME	BB	2003/0111729 A1	06/19/2003	Leu et al.	—

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Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³	Number ⁴ Kind Code ² (if known)				

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
CME	BC	Duch et al., "Development and Characterization of Co-Ni Alloys for Microsystems Applications," <i>Journal of the Electrochemical Society</i> , 2002, 149(4), pp. C201-C208.	
CME	BD	Homma et al., "Microstructural Study of Electroless-Plated CoNiP Ternary Alloy Films for Perpendicular Magnetic Recording Media," <i>IEEE Transactions on Magnetics</i> , November 1991, 27(6), pp. 4909-4911.	
CME	BE	Kohn et al., "Characterization of Electroless Deposited Co(W,P) Thin Films for Encapsulation of Copper Metallization," <i>Materials Science and Engineering</i> , 2001, A302, pp. 18-25.	
CME	BF	Kohn et al., "Evaluation of Electroless Deposited Co(W,P) Thin Films as Diffusion Barriers for Copper Metallization," <i>Microelectronic Engineering</i> , 2001, 55, pp. 297-303.	
CME	BG	Petrov et al., "Electrochemical Study of the Electroless Deposition of Co(P) and Co (W,P) Alloys," <i>Journal of the Electrochemical Society</i> , 2002, 149(4), C187-C194.	
CME	BH	Osaka et al., "Fabrication of Electroless NiReP Barrier Layer on SiO ₂ without Sputtered Seed Layer," <i>Electrochemical and Solid-State Letters</i> , 2002, 5(1), pp. C7-C10.	
CME	BI	O'Sullivan et al., "Electrolessly Deposited Diffusion Barriers for Microelectronics," <i>IBM Journal of Research and Development</i> , September 1998, Vol. 42, No. 5, pp. 607-620.	
CME	BJ	Segawa et al., "Manufacturing-ready Selectivity of CoWP Capping on Damascene Copper Interconnects," <i>Advanced Metallization Conference 2001, AMC 2001 Proceedings of the Conference</i> , pp. 567-572.	
CME	BK	Shacham-Diamand et al., "Electroless Co(W,P) and Co (Mo,P) Deposition for Cu Metallization Applications," <i>IEEE, 2001 6th International Conference on Solid State and Integrated Circuit Technology</i> , Vol. 1, 2001, pp. 410-415.	
CME	BL	Shacham-Diamand et al., "Electroless Deposition of Thin-Film Cobalt-Tungsten-Phosphorus Layers Using Tungsten Phosphoric Acid (H ₃ P(W ₃ O ₁₀) ₄) for ULSI and MEMS Application," <i>Journal of the Electrochemical Society</i> , 2001, 148(3), pp. C162-C167.	
CME	BM	Shacham-Diamand et al., "Material Properties of Electroless 100-200 nm Thick CoWP Films," <i>Electrochemical Technology Applications in Electronics Proceedings of the Third International Symposium Electrochemical Society Proceedings</i> , 2000, Vol. 99-34, pp. 102-110.	

Examiner Signature	C. Everhart	Date Considered	10-29-04
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